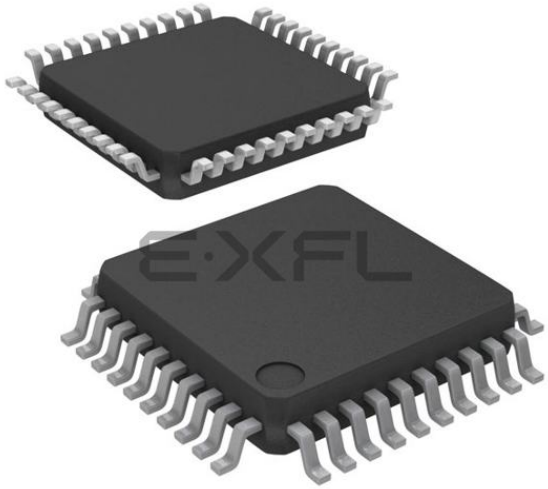

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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	LED, POR, Voltage Detect, WDT
Number of I/O	25
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.2V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21274snfp-v2

Table 1.4 Product Information for R8C/27 Group Current of Sep. 2008

Part No.	ROM Capacity		RAM Capacity	Package Type	Remarks	
	Program ROM	Data flash				
R5F21272SNFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version	
R5F21274SNFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SNFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SNFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SDFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version	
R5F21274SDFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SDFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SDFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274JFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	J version	
R5F21276JFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274KFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	K version	
R5F21276KFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SNXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	N version	Factory programming product(1)
R5F21274SNXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SNXXXFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SNXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21272SDXXXFP	8 Kbytes	1 Kbyte × 2	512 bytes	PLQP0032GB-A	D version	
R5F21274SDXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A		
R5F21275SDXXXFP	24 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21276SDXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274JXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	J version	
R5F21276JXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		
R5F21274KXXXFP	16 Kbytes	1 Kbyte × 2	1 Kbyte	PLQP0032GB-A	K version	
R5F21276KXXXFP	32 Kbytes	1 Kbyte × 2	1.5 Kbytes	PLQP0032GB-A		

NOTE:
1. The user ROM is programmed before shipment.

1.6 Pin Functions

Table 1.5 lists Pin Functions.

Table 1.5 Pin Functions

Type	Symbol	I/O Type	Description
Power supply input	VCC, VSS	I	Apply 2.2 to 5.5 V (J, K version are 2.7 to 5.5 V) to the VCC pin. Apply 0 V to the VSS pin.
Analog power supply input	AVCC, AVSS	I	Power supply for the A/D converter. Connect a capacitor between AVCC and AVSS.
Reset input	$\overline{\text{RESET}}$	I	Input “L” on this pin resets the MCU.
MODE	MODE	I	Connect this pin to VCC via a resistor.
XIN clock input	XIN	I	These pins are provided for XIN clock generation circuit I/O. Connect a ceramic resonator or a crystal oscillator between the XIN and XOUT pins. To use an external clock, input it to the XIN pin and leave the XOUT pin open.
XIN clock output	XOUT	O	
XCIN clock input (N, D version)	XCIN	I	These pins are provided for XCIN clock generation circuit I/O. Connect a crystal oscillator between the XCIN and XCOUT pins. To use an external clock, input it to the XCIN pin and leave the XCOUT pin open.
XCIN clock output (N, D version)	XCOUT	O	
$\overline{\text{INT}}$ interrupt input	$\overline{\text{INT0}}$, $\overline{\text{INT1}}$, $\overline{\text{INT3}}$	I	$\overline{\text{INT}}$ interrupt input pins
Key input interrupt	$\overline{\text{KI0}}$ to $\overline{\text{KI3}}$	I	Key input interrupt input pins
Timer RA	TRAO	O	Timer RA output pin
	TRAIO	I/O	Timer RA I/O pin
Timer RB	TRBO	O	Timer RB output pin
Timer RC	TRCCLK	I	External clock input pin
	TRCTRG	I	External trigger input pin
	TRCIOA, TRCIOB, TRCIOC, TRCIOD	I/O	Sharing output-compare output / input-capture input / PWM / PWM2 output pins
Timer RE	TREO	O	Timer RE output pin
Serial interface	CLK0, CLK1	I/O	Clock I/O pin
	RXD0, RXD1	I	Receive data input pin
	TXD0, TXD1	O	Transmit data output pin
I^2C bus interface	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
Clock synchronous serial I/O with chip select	SSI	I/O	Data I/O pin
	$\overline{\text{SCS}}$	I/O	Chip-select signal I/O pin
	SSCK	I/O	Clock I/O pin
	SSO	I/O	Data I/O pin
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter
A/D converter	AN0 to AN11	I	Analog input pins to A/D converter
I/O port	P0_0 to P0_7, P1_0 to P1_7, P3_1, P3_3 to P3_7, P4_5, P5_3, P5_4	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program. P1_0 to P1_7 also function as LED drive ports (N, D version).
Input port	P4_2, P4_6, P4_7	I	Input-only ports

I: Input O: Output I/O: Input and output

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}	–	–	10	Bits
–	Absolute accuracy	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±3	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±2	LSB
		10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±5	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±2	LSB
		10-bit mode	ϕ_{AD} = 5 MHz, V_{ref} = AV_{CC} = 2.2 V	–	–	±5	LSB
		8-bit mode	ϕ_{AD} = 5 MHz, V_{ref} = AV_{CC} = 2.2 V	–	–	±2	LSB
R_{ladder}	Resistor ladder		V_{ref} = AV_{CC}	10	–	40	kΩ
t_{conv}	Conversion time	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	3.3	–	–	µs
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	2.8	–	–	µs
V_{ref}	Reference voltage			2.2	–	AV_{CC}	V
V_{IA}	Analog input voltage(2)			0	–	AV_{CC}	V
–	A/D operating clock frequency	Without sample and hold	V_{ref} = AV_{CC} = 2.7 to 5.5 V	0.25	–	10	MHz
		With sample and hold	V_{ref} = AV_{CC} = 2.7 to 5.5 V	1	–	10	MHz
		Without sample and hold	V_{ref} = AV_{CC} = 2.2 to 5.5 V	0.25	–	5	MHz
		With sample and hold	V_{ref} = AV_{CC} = 2.2 to 5.5 V	1	–	5	MHz

NOTES:
1. AV_{CC} = 2.2 to 5.5 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

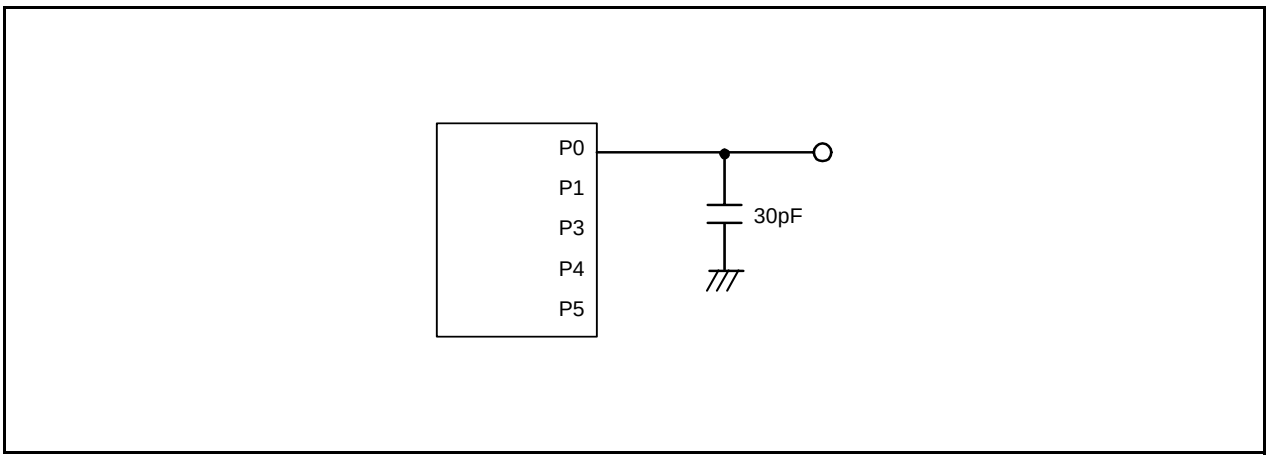
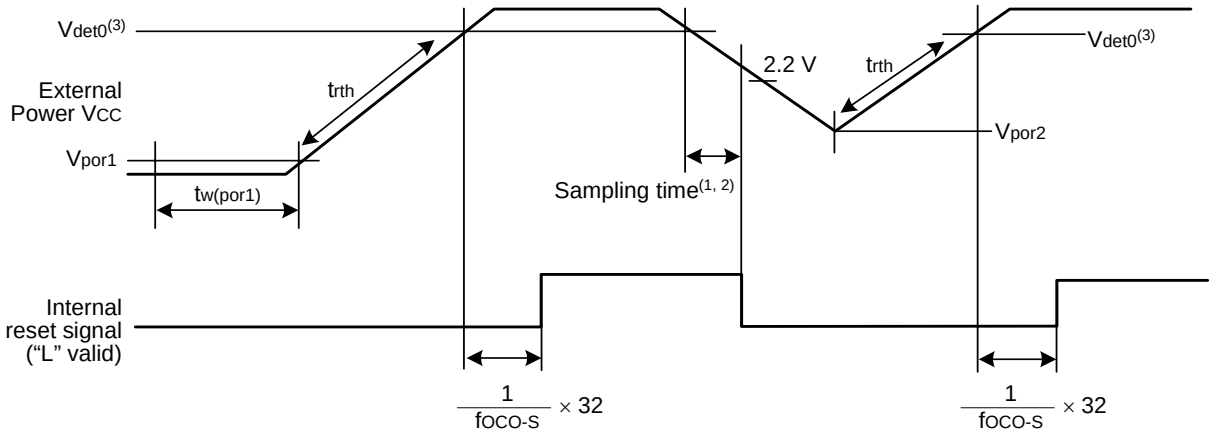


Figure 5.1 Ports P0, P1, and P3 to P5 Timing Measurement Circuit

Table 5.9 Power-on Reset Circuit, Voltage Monitor 0 Reset Electrical Characteristics(3)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{por1}	Power-on reset valid voltage(4)		–	–	0.1	V
V_{por2}	Power-on reset or voltage monitor 0 reset valid voltage		0	–	V_{det0}	V
t_{rth}	External power V_{CC} rise gradient(2)		20	–	–	mV/msec

NOTES:
1. The measurement condition is T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. This condition (external power V_{CC} rise gradient) does not apply if $V_{CC} \geq 1.0$ V.
3. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVD0ON bit in the OFS register to 0, the VW0C0 and VW0C6 bits in the VW0C register to 1 respectively, and the VCA25 bit in the VCA2 register to 1.
4. $t_{w(por1)}$ indicates the duration the external power V_{CC} must be held below the effective voltage (V_{por1}) to enable a power on reset. When turning on the power for the first time, maintain $t_{w(por1)}$ for 30 s or more if -20°C ≤ T_{opr} ≤ 85°C, maintain $t_{w(por1)}$ for 3,000 s or more if -40°C ≤ T_{opr} < -20°C.



NOTES:
1. When using the voltage monitor 0 digital filter, ensure that the voltage is within the MCU operation voltage range (2.2 V or above) during the sampling time.
2. The sampling clock can be selected. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.
3. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** of Hardware Manual for details.

Figure 5.3 Reset Circuit Electrical Characteristics

Table 5.10 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 4.75 to 5.25 V 0°C ≤ T_{opr} ≤ 60°C(2)	39.2	40	40.8	MHz
		V_{CC} = 3.0 to 5.5 V -20°C ≤ T_{opr} ≤ 85°C(2)	38.8	40	41.2	MHz
		V_{CC} = 3.0 to 5.5 V -40°C ≤ T_{opr} ≤ 85°C(2)	38.4	40	41.6	MHz
		V_{CC} = 2.7 to 5.5 V -20°C ≤ T_{opr} ≤ 85°C(2)	38	40	42	MHz
		V_{CC} = 2.7 to 5.5 V -40°C ≤ T_{opr} ≤ 85°C(2)	37.6	40	42.4	MHz
		V_{CC} = 2.2 to 5.5 V -20°C ≤ T_{opr} ≤ 85°C(3)	35.2	40	44.8	MHz
		V_{CC} = 2.2 to 5.5 V -40°C ≤ T_{opr} ≤ 85°C(3)	34	40	46	MHz
		V_{CC} = 5.0 V ± 10% -20°C ≤ T_{opr} ≤ 85°C(2)	38.8	40	40.8	MHz
		V_{CC} = 5.0 V ± 10% -40°C ≤ T_{opr} ≤ 85°C(2)	38.4	40	40.8	MHz
	High-speed on-chip oscillator frequency when correction value in FRA7 register is written to FRA1 register(4)	V_{CC} = 5.0 V, T_{opr} = 25°C	–	36.864	–	MHz
		V_{CC} = 3.0 to 5.5 V -20°C ≤ T_{opr} ≤ 85°C	-3%	–	3%	%
–	Value in FRA1 register after reset		08h(3)	–	F7h(3)	–
–	Oscillation frequency adjustment unit of high-speed on-chip oscillator	Adjust FRA1 register (value after reset) to -1	–	+0.3	–	MHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	400	–	µA

NOTES:
1. V_{CC} = 2.2 to 5.5 V, T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. These standard values show when the FRA1 register value after reset is assumed.
3. These standard values show when the corrected value of the FRA6 register is written to the FRA1 register.
4. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.11 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		30	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.2 to 5.5 V, T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.

Table 5.12 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.2 to 5.5 V and T_{opr} = 25°C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until system clock supply starts after the interrupt is acknowledged to exit stop mode.

Table 5.13 Timing Requirements of Clock Synchronous Serial I/O with Chip Select(1)

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	–	t_{CYC}(2)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC}(2)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC}(2)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		1t_{CYC} + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		1t_{CYC} + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1	t_{CYC}(2)
t_{SA}	SSI slave access time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	1.5t_{CYC} + 100	ns
			2.2 V ≤ V_{CC} < 2.7 V	–	–	1.5t_{CYC} + 200	ns
t_{OR}	SSI slave out open time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	1.5t_{CYC} + 100	ns
			2.2 V ≤ V_{CC} < 2.7 V	–	–	1.5t_{CYC} + 200	ns

NOTES:
1. V_{CC} = 2.2 to 5.5 V, V_{SS} = 0 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. 1t_{CYC} = 1/f1(s)

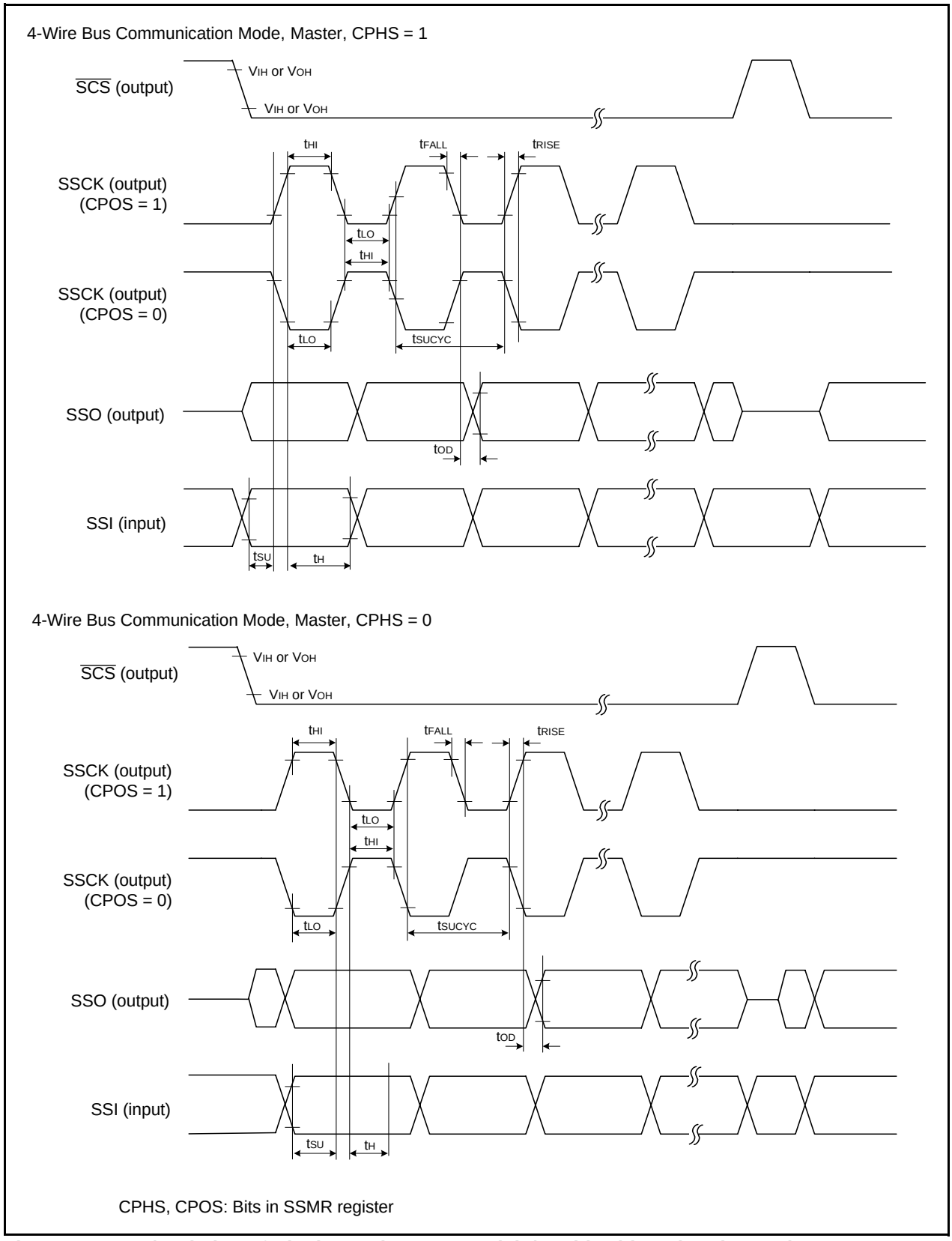


Figure 5.4 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

Table 5.14 Timing Requirements of I²C bus Interface(1)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{SCL}	SCL input cycle time		$12t_{CYC} + 600$(2)	–	–	ns
t_{SCLH}	SCL input “H” width		$3t_{CYC} + 300$(2)	–	–	ns
t_{SCLL}	SCL input “L” width		$5t_{CYC} + 500$(2)	–	–	ns
t_{sf}	SCL, SDA input fall time		–	–	300	ns
t_{SP}	SCL, SDA input spike pulse rejection time		–	–	$1t_{CYC}$(2)	ns
t_{BUF}	SDA input bus-free time		$5t_{CYC}$(2)	–	–	ns
t_{STAH}	Start condition input hold time		$3t_{CYC}$(2)	–	–	ns
t_{STAS}	Retransmit start condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{STOP}	Stop condition input setup time		$3t_{CYC}$(2)	–	–	ns
t_{SDAS}	Data input setup time		$1t_{CYC} + 20$(2)	–	–	ns
t_{SDAH}	Data input hold time		0	–	–	ns

NOTES:
1. V_{CC} = 2.2 to 5.5 V, V_{SS} = 0 V and T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.
2. $1t_{CYC} = 1/f1(s)$

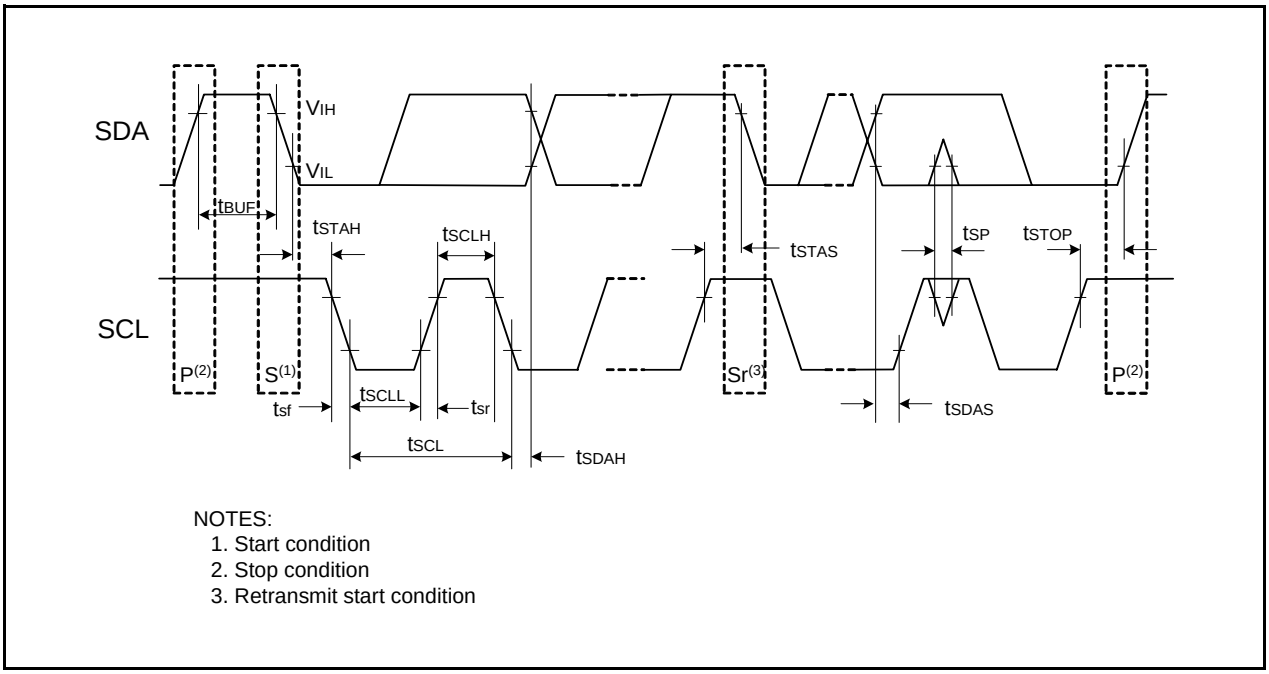


Figure 5.7 I/O Timing of I²C bus Interface

Table 5.20 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	–	ns
$t_{W(CKH)}$	CLKi input “H” width	100	–	ns
$t_{W(CKL)}$	CLKi input “L” width	100	–	ns
$t_{d(C-Q)}$	TXDi output delay time	–	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	–	ns
$t_{su(D-C)}$	RXDi input setup time	50	–	ns
$t_{h(C-D)}$	RXDi input hold time	90	–	ns

i = 0 or 1

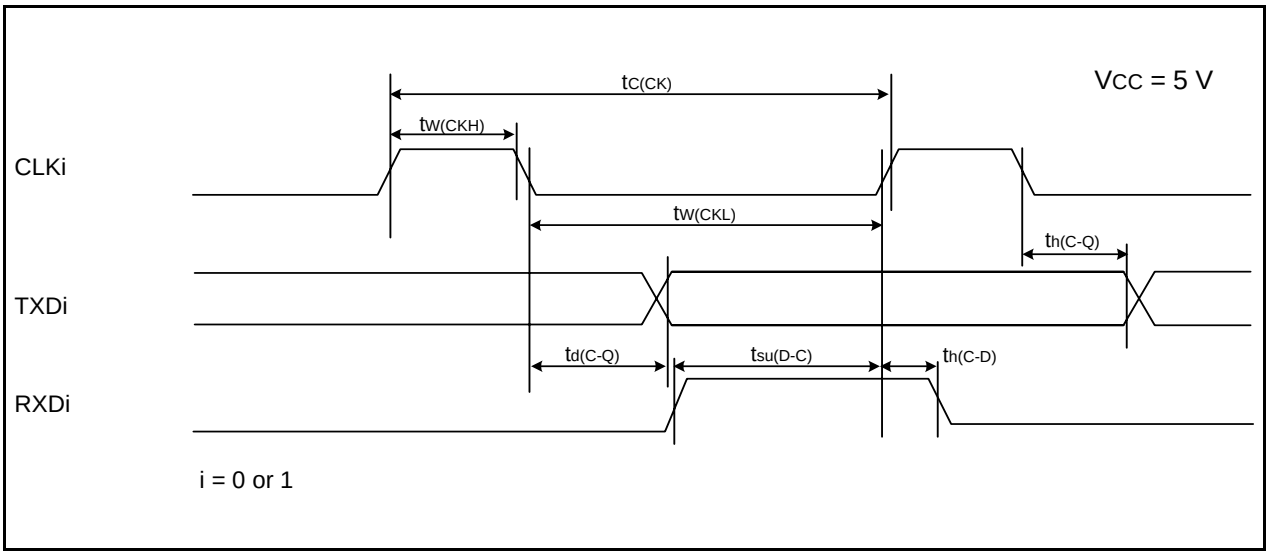


Figure 5.10 Serial Interface Timing Diagram when VCC = 5 V

Table 5.21 External Interrupt $\overline{INTi}$ (i = 0, 1, 3) Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width	250(1)	–	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width	250(2)	–	ns

NOTES:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

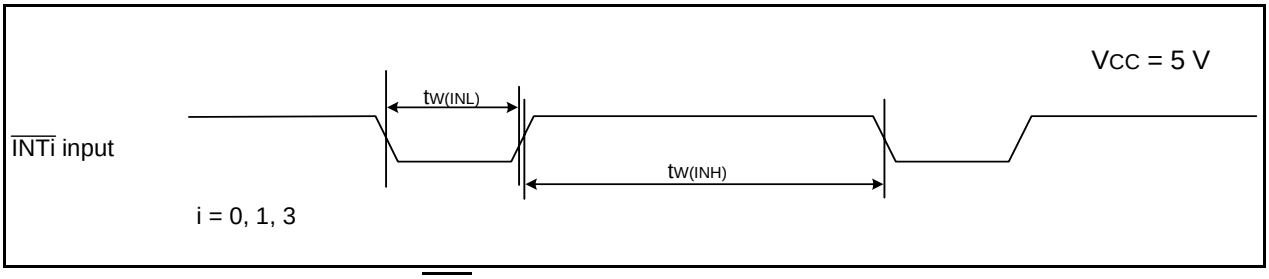


Figure 5.11 External Interrupt $\overline{INTi}$ Input Timing Diagram when VCC = 5 V

Table 5.22 Electrical Characteristics (3) [V_{CC} = 3 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P1_0 to P1_7, XOUT	I_{OH} = -1 mA		V_{CC} - 0.5	–	V_{CC}	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OH} = -5 mA	V_{CC} - 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -1 mA	V_{CC} - 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	V_{CC} - 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -50 µA	V_{CC} - 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OL} = 5 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, V_{CC} = 3 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 3 V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 3 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	18	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. V_{CC} = 2.7 to 3.3 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 10 MHz, unless otherwise specified.

Table 5.28 Electrical Characteristics (5) [Vcc = 2.2 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except P1_0 to P1_7, XOUT	I_{OH} = -1 mA		Vcc - 0.5	–	Vcc	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OH} = -2 mA	Vcc - 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = -1 mA	Vcc - 0.5	–	Vcc	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	Vcc - 0.5	–	Vcc	V
			Drive capacity LOW	I_{OH} = -50 µA	Vcc - 0.5	–	Vcc	V
V_{OL}	Output “L” voltage	Except P1_0 to P1_7, XOUT	I_{OL} = 1 mA		–	–	0.5	V
		P1_0 to P1_7	Drive capacity HIGH	I_{OL} = 2 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 1 mA	–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 µA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.05	0.3	–	V
		$\overline{RESET}$			0.05	0.15	–	V
I_{IH}	Input “H” current		VI = 2.2 V		–	–	4.0	µA
I_{IL}	Input “L” current		VI = 0 V		–	–	-4.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V		100	200	600	kΩ
R_{fXIN}	Feedback resistance	XIN			–	5	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN			–	35	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	–	–	V

NOTE:
1. Vcc = 2.2 V at T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), f(XIN) = 5 MHz, unless otherwise specified.

Table 5.29 Electrical Characteristics (6) [Vcc = 2.2 V]
(T_{opr} = -20 to 85°C (N version) / -40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
I_{CC}	Power supply current (V_{CC} = 2.2 to 2.7 V) Single-chip mode, output pins are open, other pins are V_{SS}	High-speed clock mode	XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN = 5 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz No division	–	3.5	–	mA
			XIN clock off High-speed on-chip oscillator on fOCO = 5 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	–	1.5	–	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR47 = 1	–	100	230	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz FMR47 = 1	–	100	230	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz Program operation on RAM Flash memory off, FMSTP = 1	–	25	–	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	22	60	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	20	55	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (high drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	3.0	–	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (low drive) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0 VCA20 = 1	–	1.8	–	µA
		Stop mode	XIN clock off, T_{opr} = 25°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	0.7	3.0	µA
			XIN clock off, T_{opr} = 85°C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	–	1.1	–	µA

Table 5.36 A/D Converter Characteristics

Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
–	Resolution		V_{ref} = AV_{CC}	–	–	10	Bits
–	Absolute accuracy	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±3	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	–	–	±2	LSB
		10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±5	LSB
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 3.3 V	–	–	±2	LSB
R_{ladder}	Resistor ladder		V_{ref} = AV_{CC}	10	–	40	kΩ
t_{conv}	Conversion time	10-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	3.3	–	–	µs
		8-bit mode	ϕ_{AD} = 10 MHz, V_{ref} = AV_{CC} = 5.0 V	2.8	–	–	µs
V_{ref}	Reference voltage			2.7	–	AV_{CC}	V
V_{IA}	Analog input voltage(2)			0	–	AV_{CC}	V
–	A/D operating clock frequency	Without sample and hold		0.25	–	10	MHz
		With sample and hold		1	–	10	MHz

NOTES:
1. AV_{CC} = 2.7 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

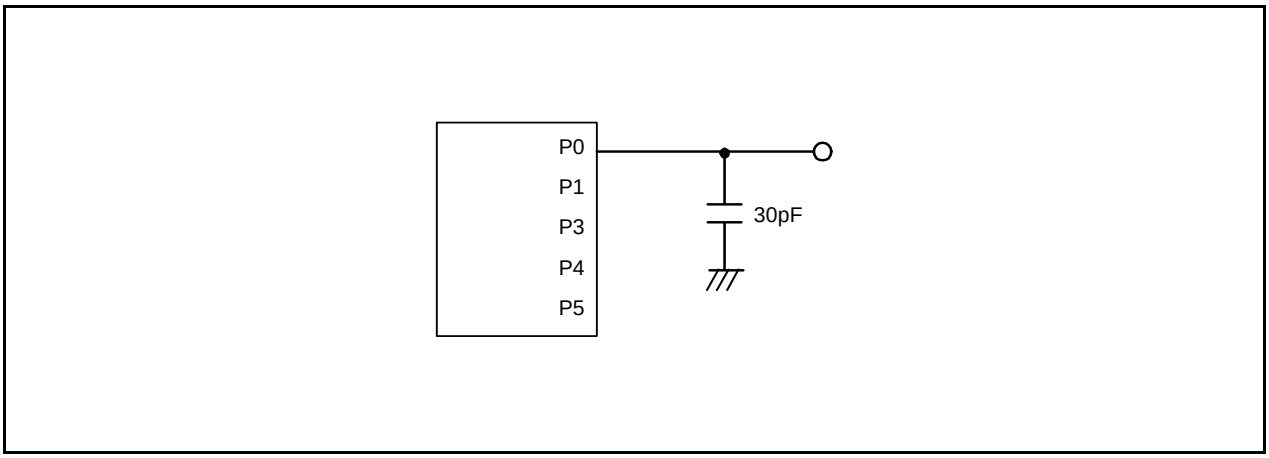


Figure 5.20 Ports P0, P1, and P3 to P5 Timing Measurement Circuit

Table 5.38 Flash Memory (Data flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	97 + CPU clock × 6 cycles	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycles	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-40	–	85(8)	°C
–	Data hold time(9)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times is the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. 125°C for K version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

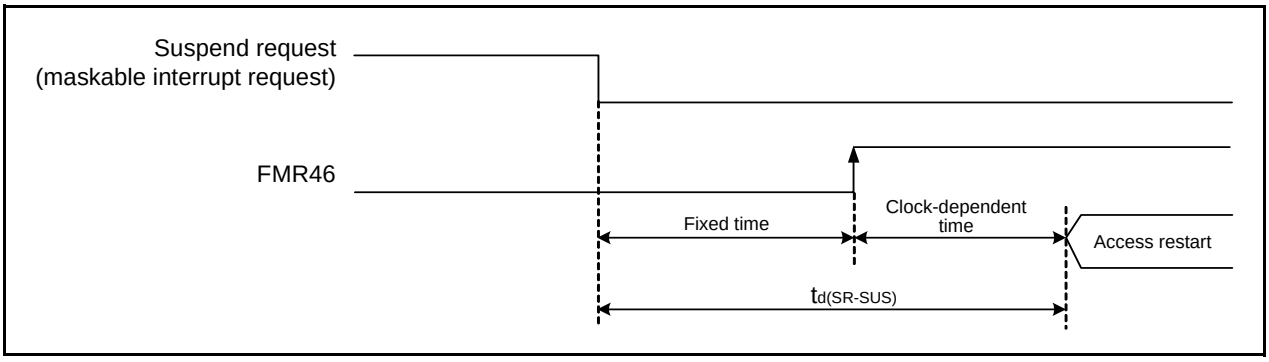


Figure 5.21 Time delay until Suspend

Table 5.39 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(2, 4)		2.70	2.85	3.0	V
$t_{d(Vdet1-A)}$	Voltage monitor 1 reset generation time(5)		–	40	200	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.70	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version).
2. Hold $V_{det2} > V_{det1}$.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
4. This parameter shows the voltage detection level when the power supply drops.
   The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.
5. Time until the voltage monitor 1 reset is generated after the voltage passes V_{det1} when V_{CC} falls. When using the digital filter, its sampling time is added to $t_{d(Vdet1-A)}$. When using the voltage monitor 1 reset, maintain this time until V_{CC} = 2.0 V after the voltage passes V_{det1} when the power supply falls.

Table 5.40 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(2)		3.3	3.6	3.9	V
$t_{d(Vdet2-A)}$	Voltage monitor 2 reset/interrupt request generation time(3, 5)		–	40	200	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(4)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version).
2. Hold $V_{det2} > V_{det1}$.
3. Time until the voltage monitor 2 reset/interrupt request is generated after the voltage passes V_{det2}.
4. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
5. When using the digital filter, its sampling time is added to $t_{d(Vdet2-A)}$. When using the voltage monitor 2 reset, maintain this time until V_{CC} = 2.0 V after the voltage passes V_{det2} when the power supply falls.

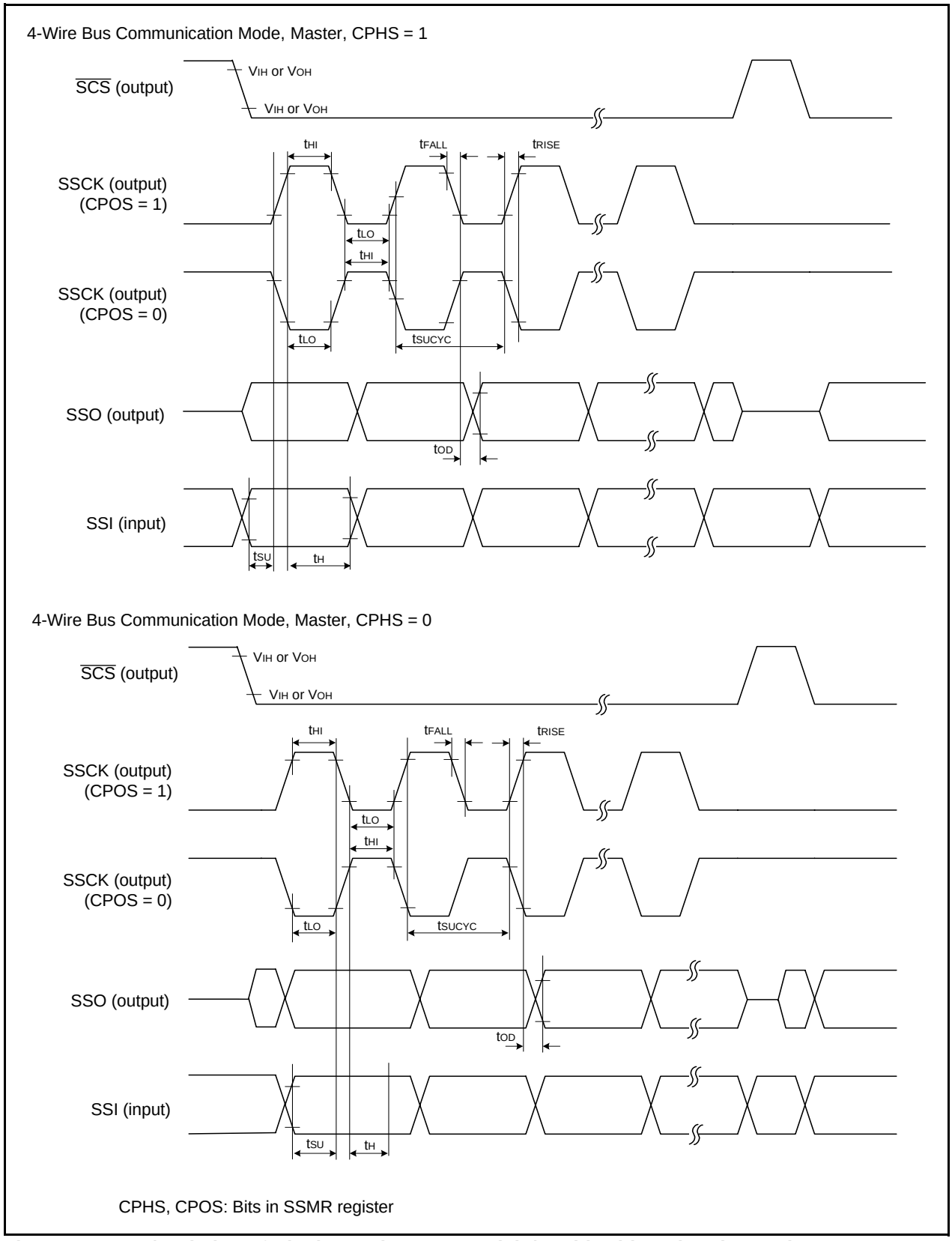


Figure 5.23 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Master)

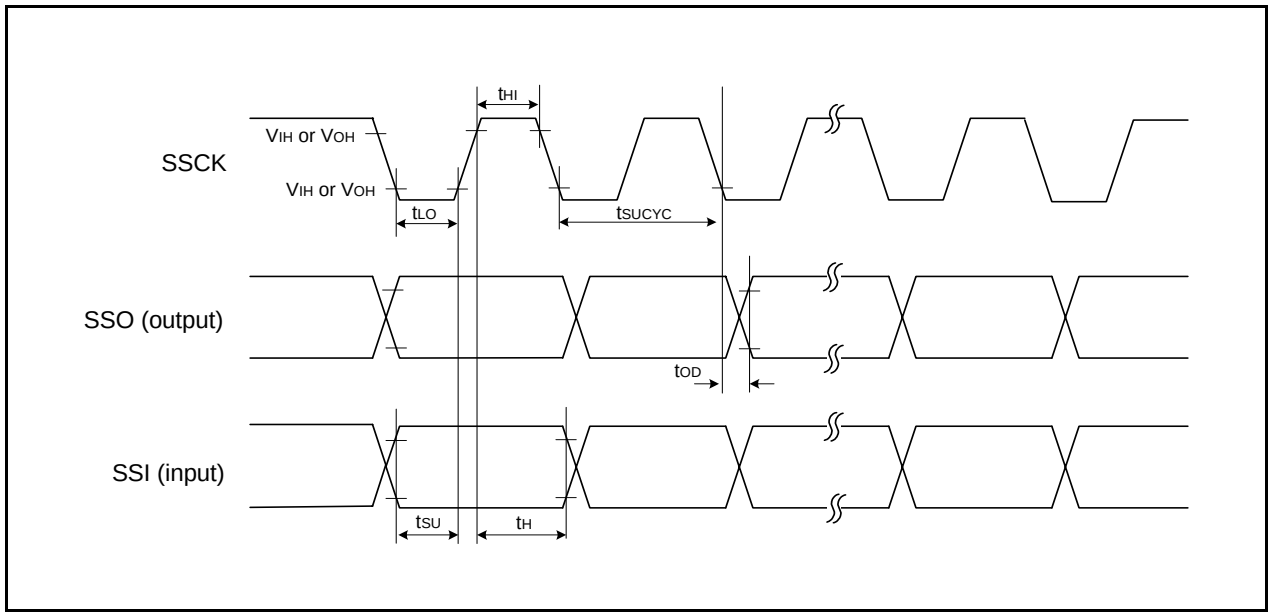


Figure 5.25 I/O Timing of Clock Synchronous Serial I/O with Chip Select (Clock Synchronous Communication Mode)

Table 5.47 Electrical Characteristics (1) [V_{CC} = 5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -5 mA		V_{CC} - 2.0	–	V_{CC}	V
			I_{OH} = -200 μA		V_{CC} - 0.3	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -1 mA	V_{CC} - 2.0	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -500 μA	V_{CC} - 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 5 mA		–	–	2.0	V
			I_{OL} = 200 μA		–	–	0.45	V
		XOUT	Drive capacity HIGH	I_{OL} = 1 mA	–	–	2.0	V
			Drive capacity LOW	I_{OL} = 500 μA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, CLK1, SSI, SCL, SDA, SSO			0.1	0.5	–	V
		$\overline{RESET}$			0.1	1.0	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5V		–	–	5.0	μA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5V		–	–	-5.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5V		30	50	167	kΩ
R_{fXIN}	Feedback resistance	XIN			–	1.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

NOTE:
1. V_{CC} = 4.2 to 5.5 V at T_{opr} = -40 to 85°C (J version) / -40 to 125°C (K version), f(XIN) = 20 MHz, unless otherwise specified.

Timing Requirements
(Unless Otherwise Specified: V_{CC} = 5 V, V_{SS} = 0 V at T_{opr} = 25°C) [V_{CC} = 5 V]

Table 5.49 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

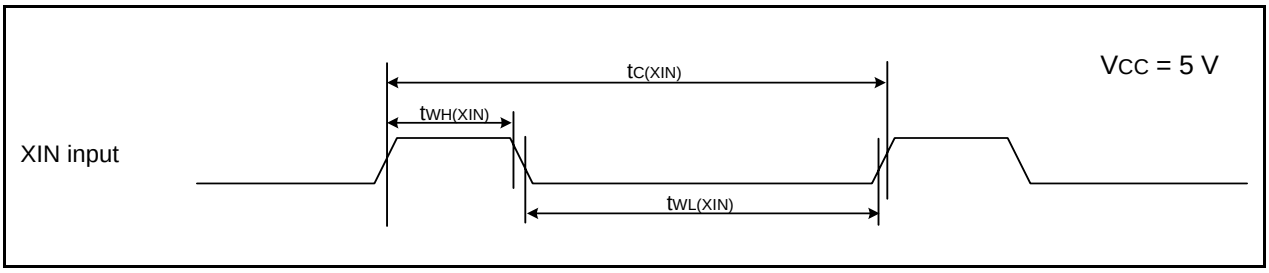


Figure 5.27 XIN Input Timing Diagram when V_{CC} = 5 V

Table 5.50 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

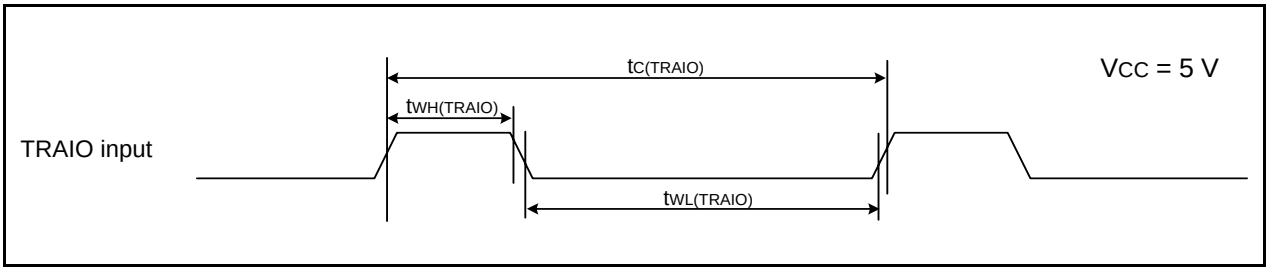


Figure 5.28 TRAIO Input Timing Diagram when V_{CC} = 5 V

REVISION HISTORY	R8C/26 Group, R8C/27 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Nov 14, 2005	–	First edition issued
0.20	Feb 06, 2006	2, 3	Table 1.1 Functions and Specifications for R8C/26Group and Table 1.2 Functions and Specifications for R8C/27 Group; Minimum instruction execution time and Supply voltage revised
		9	Table 1.6 Pin Name Information by Pin Number; "XOUT" → "XOUT/XCOUT" and "XIN" → "XIN/XCIN" revised
		18	Table 4.4 SFR Information (4); 00FEh: "DRR" → "P1DRR" revised
		19	Table 4.5 SFR Information (5); -0119h: "Timer RE Minute Data Register / Compare Register" → "Timer RE Minute Data Register / Compare Data Register" -011Ah: "Timer RE Time Data Register" → "Timer RE Hour Data Register" -011Bh: "Timer RE Day Data Register" → "Timer RE Day of Week Data Register" revised
		22 to 45	5. Electrical Characteristics added
1.00	Nov 08, 2006	All pages	"Preliminary" deleted
		2	Table 1.1 revised
		3	Table 1.2 revised
		4	Figure 1.1 revised
		5	Table 1.3 revised
		6	Table 1.4 revised
		7	Figure 1.4 revised
		9	Table 1.6 revised
		15	Table 4.1; • 001Ch: "00h" → "00h, 10000000b" revised • 000Fh: "000XXXXXb" → "00X11111b" revised • 0029h: "High-Speed On-Chip Oscillator Control Register 4, FRA4, When shipping" added • 002Bh: "High-Speed On-Chip Oscillator Control Register 6, FRA6, When shipping" added • 0032h: "00h, 01000000b" → "00h, 00100000b" revised • 0038h: "00001000b, 01001001b" → "0000X000b, 0100X001b" revised • NOTE3 and 4 revised; NOTE6 added
		18	Table 4.4; • 00E0h, 00E1h, 00E5h, 00E8h, 00E9h: "XXh" → "00h" revised • 00FDh: "XX00000000b" → "00h" revised
		22	Table 5.2 revised
		23	Figure 5.1 title revised
		24	Table 5.4 revised
		25	Table 5.5 revised
		26	Figure 5.2 title revised and Table 5.7 NOTE4 added